XN04311 (XN4311)

Silicon NPN epitaxial planer transistor (Tr1) Silicon PNP epitaxial planer transistor (Tr2)

For switching/digital circuits

Features

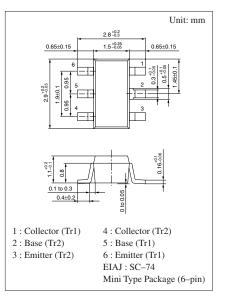
- Two elements incorporated into one package. (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

• UNR1211(UN1211) + UNR1111(UN1111)

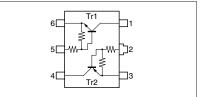
Parameter		Symbol Ratings		Unit	
Tr1	Collector to base voltage	V _{CBO}	50	V	
	Collector to emitter voltage	V _{CEO}	50	V	
	Collector current	I _C	100	mA	
Tr2	Collector to base voltage	V _{CBO}	-50	V	
	Collector to emitter voltage	V _{CEO}	-50	V	
	Collector current	I _C	-100	mA	
Overall	Total power dissipation	P _T	300	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	

Absolute Maximum Ratings (Ta=25°C)



Marking Symbol: 7X

Internal Connection



Note.) The Part number in the Parenthesis shows conventional part number.

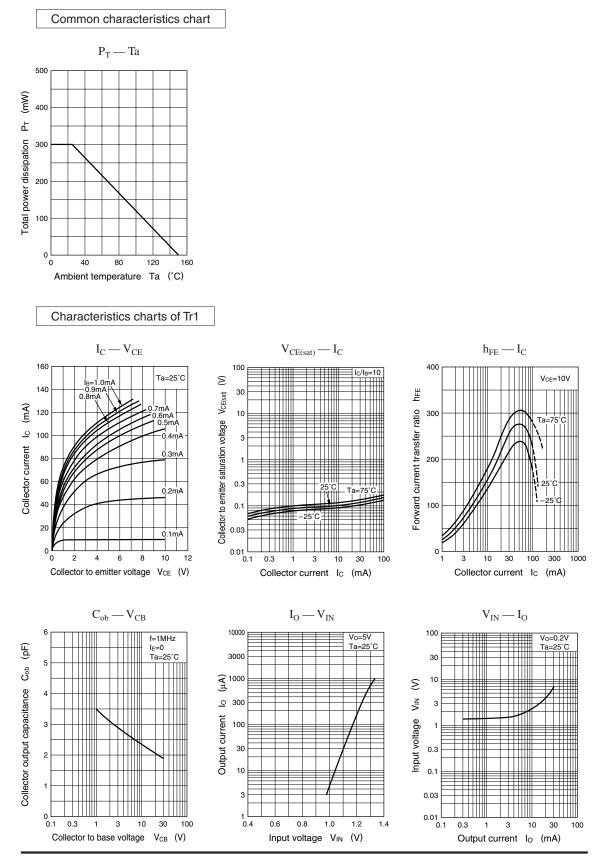
Electrical Characteristics (Ta=25°C)

• Tr1

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{C} = 10 \mu A, I_{E} = 0$	50			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 2mA, I_{\rm B} = 0$	50			V
Collector cutoff current	I _{CBO}	$V_{CB} = 50V, I_E = 0$			0.1	μΑ
	I _{CEO}	$V_{CE} = 50V, I_B = 0$			0.5	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = 6V, I_C = 0$			0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = 10V, I_C = 5mA$	35			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0.3 {\rm mA}$			0.25	V
Output voltage high level	V _{OH}	$V_{CC} = 5V, V_B = 0.5V, R_L = 1k\Omega$	4.9			V
Output voltage low level	V _{OL}	$V_{CC} = 5V, V_B = 2.5V, R_L = 1k\Omega$			0.2	V
Transition frequency	f _T	$V_{CB} = 10V, I_E = -1mA, f = 200MHz$		150		MHz
Input resistance	R ₁		-30%	10	+30%	kΩ
Resistance ratio	R_1/R_2		0.8	1.0	1.2	

• Tr2

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-50			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = -2mA, I_{\rm B} = 0$	-50			V
	I _{CBO}	$V_{CB} = -50V, I_E = 0$			- 0.1	μΑ
Collector cutoff current	I _{CEO}	$V_{CE} = -50V, I_B = 0$			- 0.5	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = -6V, I_C = 0$			- 0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10V, I_C = -5mA$	35			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -0.3 {\rm mA}$			- 0.25	V
Output voltage high level	V _{OH}	$V_{CC} = -5V, V_B = -0.5V, R_L = 1k\Omega$	-4.9			V
Output voltage low level	V _{OL}	$V_{CC} = -5V, V_B = -2.5V, R_L = 1k\Omega$			- 0.2	V
Transition frequency	f _T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Input resistance	R ₁		-30%	10	+30%	kΩ
Resistance ratio	R ₁ /R ₂		0.8	1.0	1.2	



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Characteristics charts of Tr2 $I_C - V_{CE}$ V_{CE(sat)} - I_C $h_{FE} - I_C$ -160 160 -100 $I_C/I_B=10$ | | -1.0mA Ta=25°C V_{CE}=-10V Σ -140 -30 hFE Collector to emitter saturation voltage VcE(sat) 0.9mA € -120 25°C Forward current transfer ratio 120 -10 -0.8mA –0.7mA –0.6mA -3 Collector current -80 -0.5mA 80 -1 ____ −0.4mA -60 + -0.3 -0.3mA -40 -0.1 40 -0.2mA -20 -0.03 -0.1mA 0 -0.01 -0.1 0 -30 -100 -300 -1000 0 -2 -4 -6 -8 -10 -12 -0.3 -3 -10 -30 -100 -1 -3 -10 -1 Collector to emitter voltage V_{CE} (V) Collector current Ic (mA) Collector current Ic (mA) $C_{ob} - V_{CB}$ $I_0 - V_{IN}$ $V_{IN} - I_O$ 6 -10000 -100 Vo=-5V 1111 Vo=-0.2V f=1MHz Ta=25°C Ta=25°C Collector output capacitance Cob (pF) $I_{E}=0$ -30 Ta=25°C -3000 5 (Y)-1000 -10 3 -1 -1 -0.3 -1 -0.3 4 Output current 3 -100 -30 2 -10 1 -3 -0.03 -0.01 0└ −0.1 -1 -0.4 -0.3 -1 -3 -10 -30 -100 -0.6 -0.8 -1.0 -1.2 -1.4 -0.3 -1 -3 -10 -30 -100 Collector to base voltage Input voltage VIN V_{CB} (V) (V) Output current Io (mA)

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